



N-Channel 30-V (D-S) MOSFET

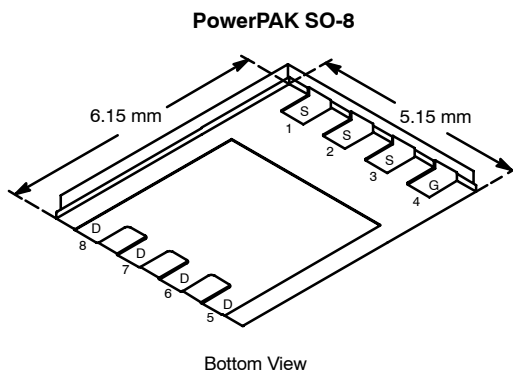
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.003 @ $V_{GS} = 10$ V	30
	0.004 @ $V_{GS} = 4.5$ V	27

FEATURES

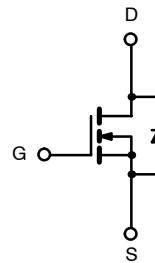
- Ultra-Low On-Resistance Using High Density TrenchFET® Gen II Power MOSFET Technology
- New Low Thermal Resistance PowerPAK® Package with Low 1.07-mm Profile

APPLICATIONS

- Low-Side DC/DC Conversion
 - Notebook
 - Server
 - Workstation
- Point-of-Load Conversion



Ordering Information: Si7356DP-T1



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	30	18	A
		$T_A = 70^\circ\text{C}$	25	15	
Pulsed Drain Current (10 μs Pulse Width)	I_{DM}	70			
Continuous Source Current (Diode Conduction) ^a	I_S	4.5	1.8		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	5.4	1.9	W
		$T_A = 70^\circ\text{C}$	3.4	1.2	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	18	23	$^\circ\text{C/W}$
		Steady State	50	65	
Maximum Junction-to-Case (Drain)	R_{thJC}	1.0	1.5		

Notes

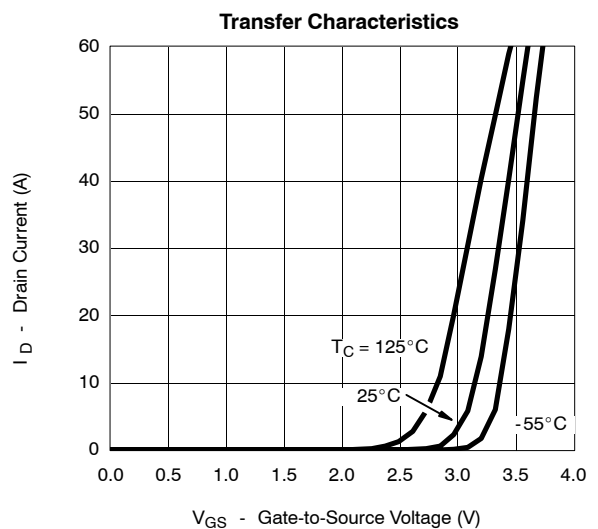
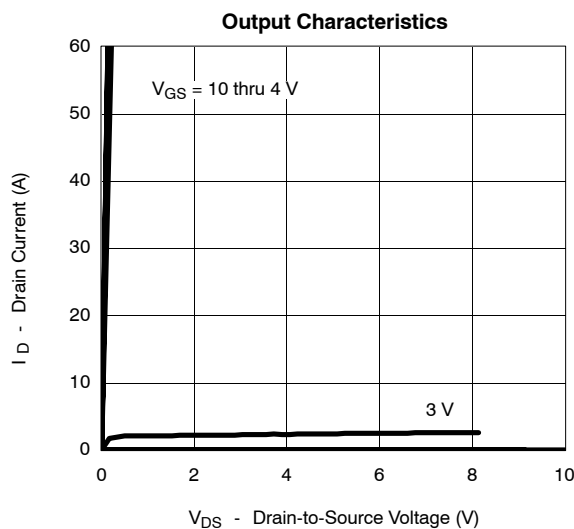
a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^{NO TAG}	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^{NO TAG}	r _{DS(on)}	V _{GS} = 10 V, I _D = 25 A		0.0024	0.003	Ω
		V _{GS} = 4.5 V, I _D = 19 A		0.0032	0.004	
Forward Transconductance ^{NO TAG}	g _{fs}	V _{DS} = 15 V, I _D = 25 A		110		S
Diode Forward Voltage ^{NO TAG}	V _{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.72	1.1	V
Dynamic^{NO TAG}						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A		45	70	nC
Gate-Source Charge	Q _{gs}			20		
Gate-Drain Charge	Q _{gd}			16		
Gate Resistance	R _G			1.1		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω		27	40	ns
Rise Time	t _r			21	35	
Turn-Off Delay Time	t _{d(off)}			107	160	
Fall Time	t _f			43	65	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, di/dt = 100 A/μs		45	70	

Notes

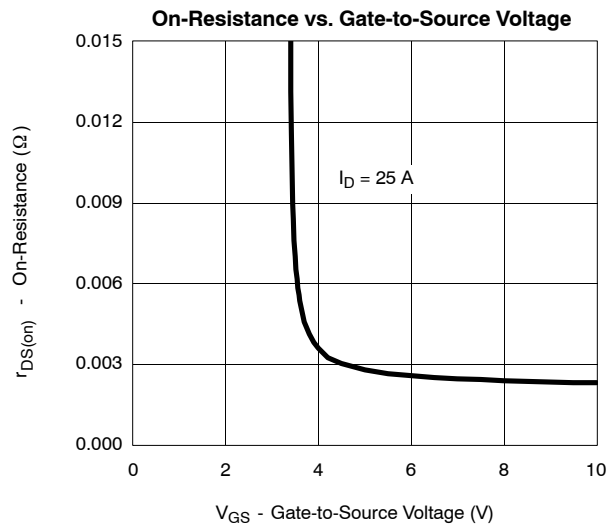
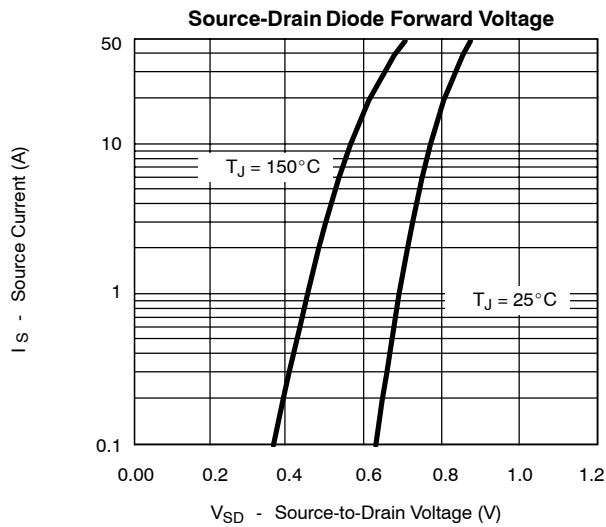
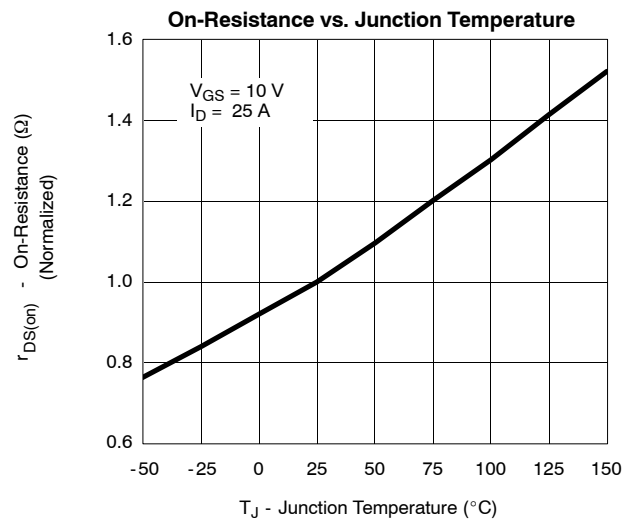
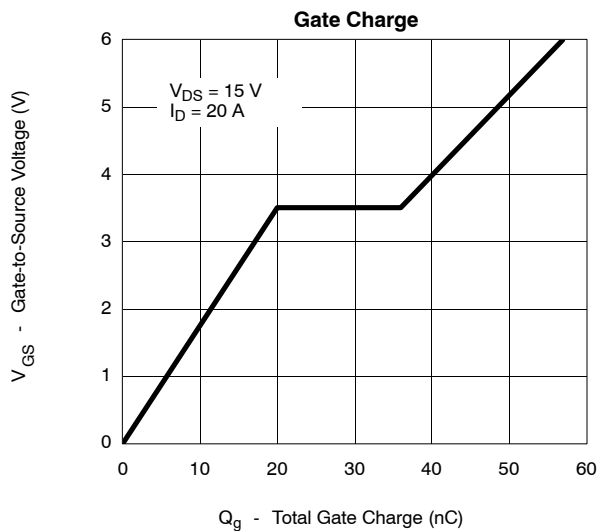
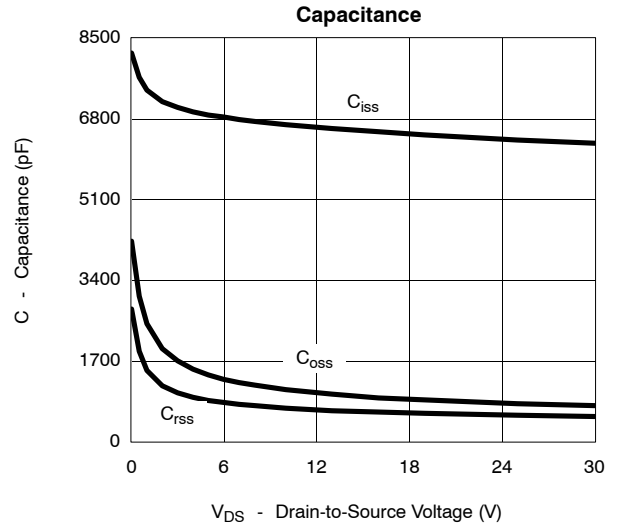
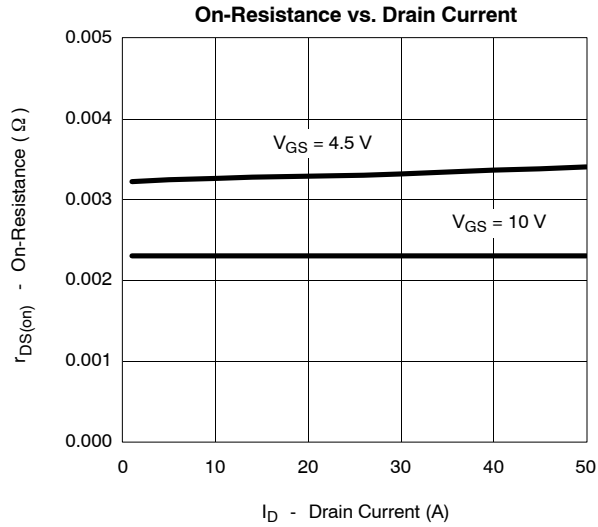
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

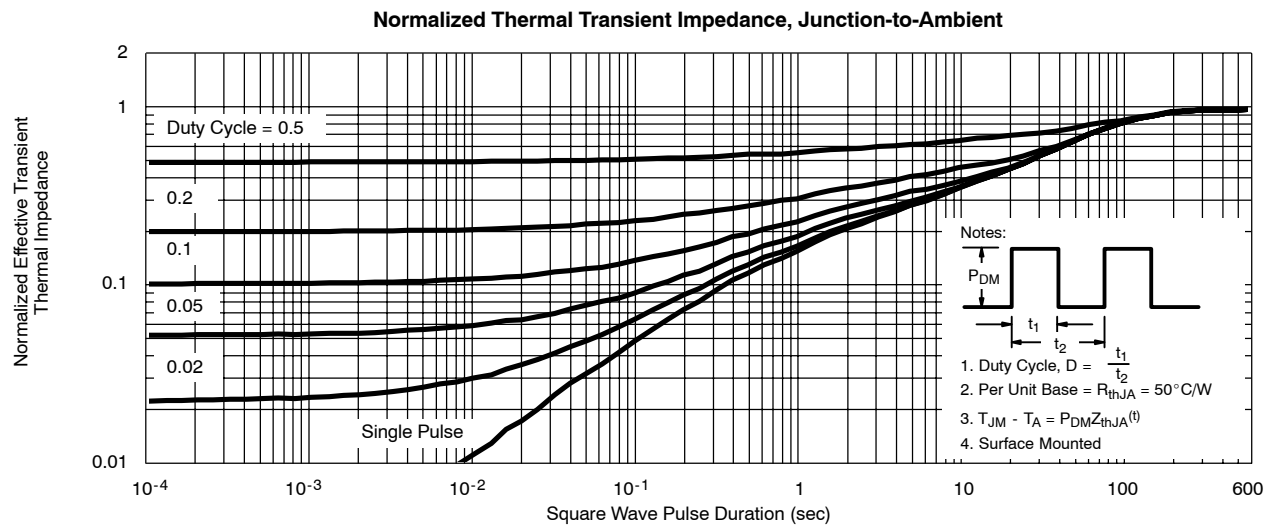
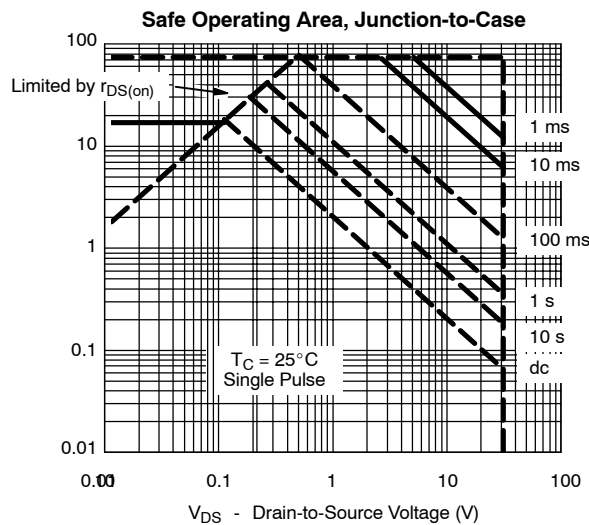
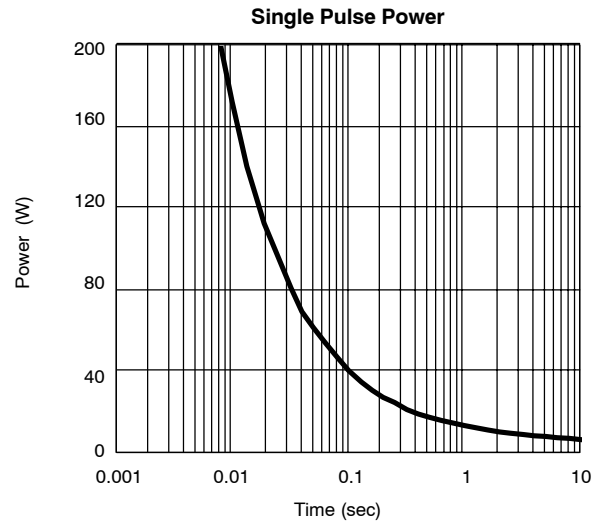
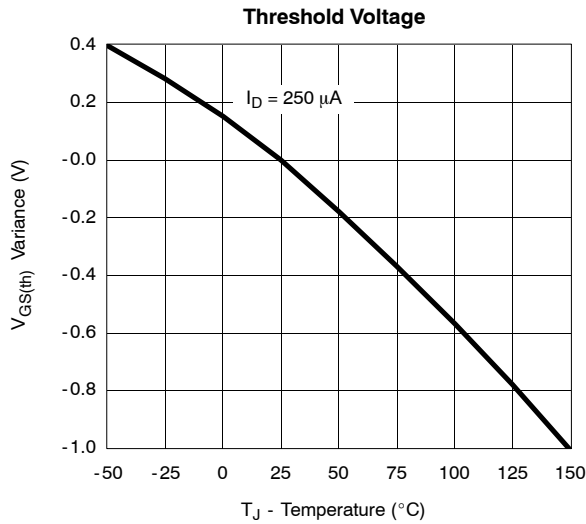




TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

